Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	84572	MISFET or MOSFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 14:55
L2	96115	(gate near insulating near film) or (gate near dielectric) or (gate near oxide)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 15:02
L3	3548	(gate near length) same thickness	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 15:02
L4	1292	l1 and l2 and l3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 15:03
L5	2754	rapid near thermal near process	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 15:06
L6	14	l4 and l5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/22 15:06